

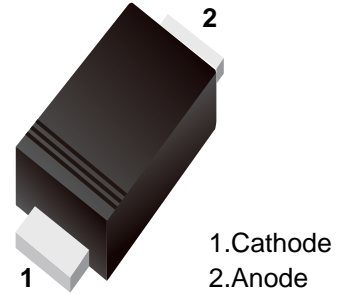


SEMICONDUCTOR

RB520S-30 Schottky Barrier Diode

Features

- Low Forward Voltage Drop
- Flat Lead SOD-523 Small Outline Plastic Package
- Matte Tin(Sn) Lead Finish



■ Simplified outline(SOD-523)

Top View

■ Marking

Marking	B
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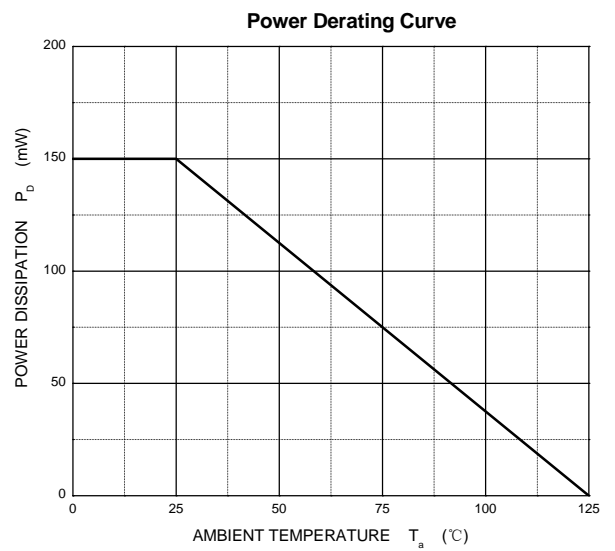
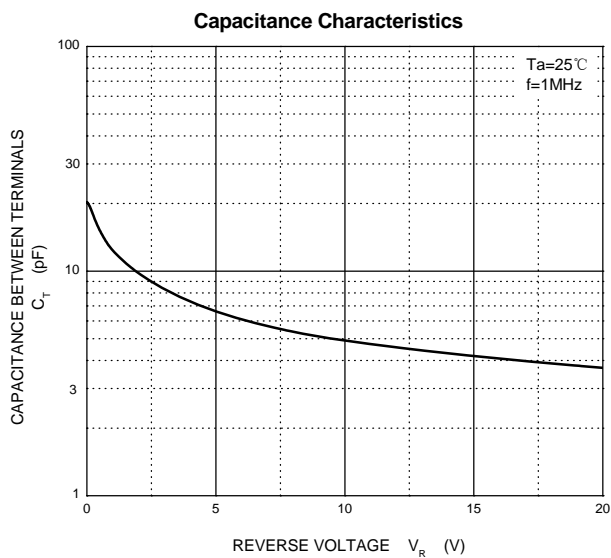
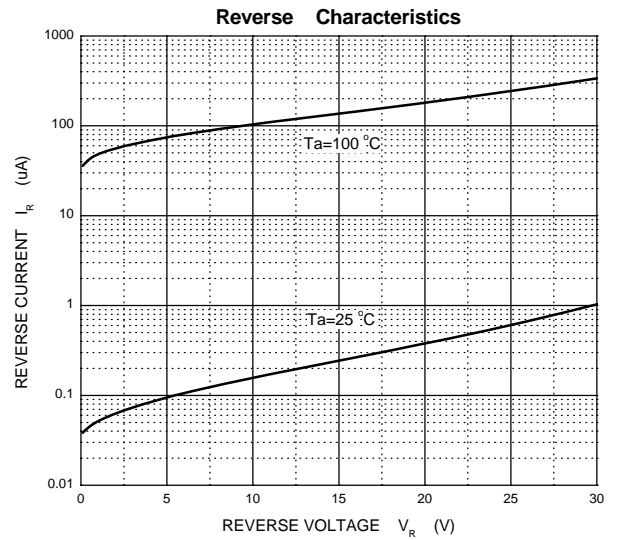
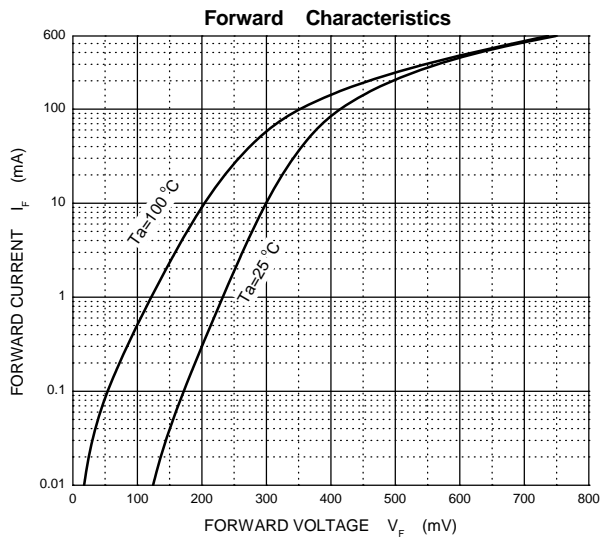
Absolute Maximum Ratings Ta = 25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	30	V
Average Rectified Output Current	$I_{F(AV)}$	200	mA
Peak Forward Surge Current (At 8.3ms single half sine-wave)	I_{FSM}	1	A
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	125	°C
Storage Temperature range	T_{stg}	-55 to +125	

Electrical Characteristics Ta = 25°C unless otherwise noted

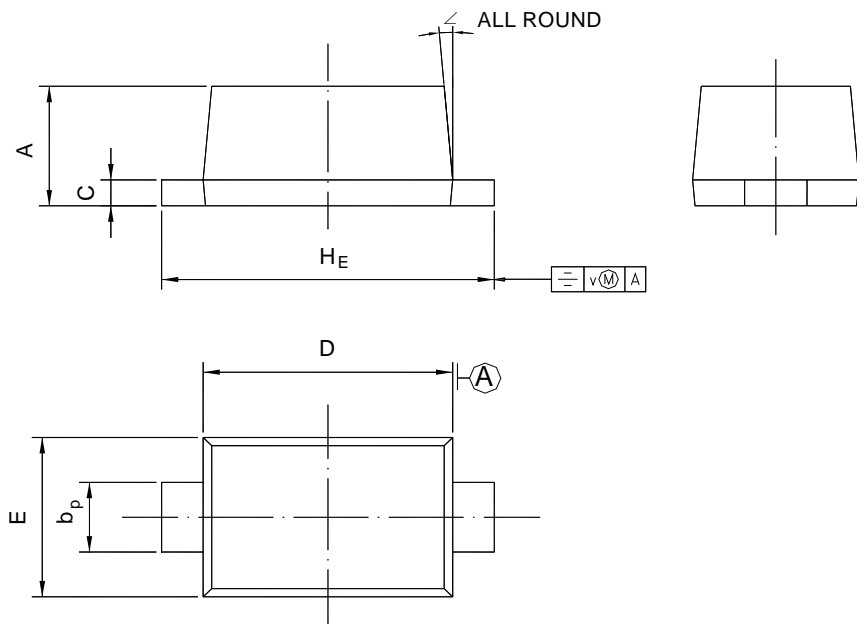
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Breakdown Voltage	B_V	$I_R = 500\mu A$	30			V
Forward voltage	V_F	$I_F = 200mA$			0.6	V
Reverse Leakage current	I_R	$V_R = 10 V$			1	μA

RB520S-30



RB520S-30

SOD-523



UNIT	A	b_p	C	D	E	H_E	V	\angle
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°